

# VS-VSKT136/14PBF Datasheet

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|                              |   |
|------------------------------|---|
| DiGi Electronics Part Number | VS-VSKT136/14PBF-DG   |
| Manufacturer                 | <a href="#">Vishay General Semiconductor - Diodes Division</a>                |
| Manufacturer Product Number  | VS-VSKT136/14PBF  |
| Description                  | MOD PH CTRL 1400V 135A INT-A-PAK  |
| Detailed Description         | SCR Module 1.4 kV 300 A Series Connection - All SC Rs Chassis Mount INT-A-Pak |

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## Purchase and inquiry

Manufacturer Product Number:

VS-VSKT136/14PBF

Series:

-

Structure:

Series Connection - All SCRs

Voltage - Off State:

1.4 kV

Current - On State (It (RMS)) (Max):

300 A

Current - Gate Trigger (Igt) (Max):

150 mA

Current - Hold (Ih) (Max):

200 mA

Mounting Type:

Chassis Mount

Base Product Number:

VSKT136

Manufacturer:

Vishay General Semiconductor - Diodes Division

Product Status:

Active

Number of SCRs, Diodes:

2 SCRs

Current - On State (It (AV)) (Max):

135 A

Voltage - Gate Trigger (Vgt) (Max):

2.5 V

Current - Non Rep. Surge 50, 60Hz (I<sub>tsm</sub>):

3200A, 3360A

Operating Temperature:

-40°C ~ 125°C (Tj)

Package / Case:

INT-A-Pak

## Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.30.0080

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99



# VS-VSK.136..PbF, VS-VSK.142..PbF, VS-VSK.162..PbF Series

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## Thyristor/Diode and Thyristor/Thyristor, 135 A to 160 A (INT-A-PAK Power Modules)



INT-A-PAK

| PRIMARY CHARACTERISTICS |                               |
|-------------------------|-------------------------------|
| $I_{T(AV)}$             | 135 A to 160 A                |
| Type                    | Modules - thyristor, standard |
| Package                 | INT-A-PAK                     |

### FEATURES

- High voltage
- Electrically isolated by DBC ceramic ( $Al_2O_3$ )
- 3500  $V_{RMS}$  isolating voltage
- Industrial standard package
- High surge capability
- Glass passivated chips
- Modules uses high voltage power thyristor/diodes in three basic configurations
- Simple mounting
- UL approved file E78996 
- Designed and qualified for multiple level
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



RoHS  
COMPLIANT

### APPLICATIONS

- DC motor control and drives
- Battery charges
- Welders
- Power converters
- Lighting control
- Heat and temperature control

| MAJOR RATINGS AND CHARACTERISTICS |                 |             |             |             |                    |
|-----------------------------------|-----------------|-------------|-------------|-------------|--------------------|
| SYMBOL                            | CHARACTERISTICS | VSK.136..   | VSK.142..   | VSK.162..   | UNITS              |
| $I_{T(AV)}$                       | 85 °C           | 135         | 140         | 160         | A                  |
| $I_{T(RMS)}$                      |                 | 300         | 310         | 355         | A                  |
| $I_{TSM}$                         | 50 Hz           | 3200        | 4500        | 4870        |                    |
|                                   | 60 Hz           | 3360        | 4712        | 5100        |                    |
| $I^2t$                            | 50 Hz           | 51.5        | 102         | 119         | kA <sup>2</sup> s  |
|                                   | 60 Hz           | 47          | 92.5        | 108         |                    |
| $I^2\sqrt{t}$                     |                 | 515.5       | 1013        | 1190        | kA <sup>2</sup> √s |
| $V_{RRM}$                         | Range           | 400 to 1600 | 400 to 1600 | 400 to 1600 | V                  |
| $T_J$                             | Range           | -40 to +125 |             |             | °C                 |

### ELECTRICAL SPECIFICATIONS

| VOLTAGE RATINGS                        |              |  |  |                                   |
|--|--------------|--|--|-----------------------------------|
| TYPE NUMBER                            | VOLTAGE CODE | $V_{RRM}/V_{DRM}$ , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE<br>V | $V_{RSM}/V_{DSM}$ , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE<br>V | $I_{RRM}/I_{DRM}$ AT 125 °C<br>mA |
| VS-VSK.136<br>VS-VSK.142<br>VS-VSK.162 | 04           | 400  | 500  | 50                                |
|  | 08           | 800  | 900  |                                   |
|  | 12           | 1200   | 1300   |                                   |
|  | 14           | 1400   | 1500   |                                   |
|  | 16           | 1600   | 1700   |                                   |



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| ON-STATE CONDUCTION  |               |  |                            |         |         |         |                    |
|--|---------------|--|----------------------------|---------|---------|---------|--------------------|
| PARAMETER  | SYMBOL        | TEST CONDITIONS  |                            | VSK.136 | VSK.142 | VSK.162 | UNITS              |
| Maximum average on-state current at case temperature           | $I_{T(AV)}$   | 180° conduction, half sine wave  |                            | 135     | 140     | 160     | A                  |
|  |               |  |                            | 85      | 85      | 85      | °C                 |
| Maximum RMS on-state current                                   | $I_{T(RMS)}$  | As AC switch   |                            | 300     | 310     | 355     | A                  |
| Maximum peak, one-cycle on-state, non-repetitive surge current | $I_{TSM}$     | t = 10 ms  | No voltage reappplied      | 3200    | 4500    | 4870    |                    |
|  |               | t = 8.3 ms   | No voltage reappplied      | 3360    | 4712    | 5100    |                    |
|  |               | t = 10 ms  | 100 % $V_{RRM}$ reappplied | 2700    | 3785    | 4100    |                    |
|  |               | t = 8.3 ms   | 100 % $V_{RRM}$ reappplied | 2800    | 3963    | 4300    |                    |
| Maximum $I^2t$ for fusing                                      | $I^2t$        | t = 10 ms  | No voltage reappplied      | 51.5    | 102     | 119     | kA <sup>2</sup> s  |
|  |               | t = 8.3 ms   | No voltage reappplied      | 47      | 92.5    | 108     |                    |
|  |               | t = 10 ms  | 100 % $V_{RRM}$ reappplied | 36.5    | 71.6    | 84      |                    |
|  |               | t = 8.3 ms   | 100 % $V_{RRM}$ reappplied | 33.3    | 65.4    | 76.7    |                    |
| Maximum $I^2\sqrt{t}$ for fusing                               | $I^2\sqrt{t}$ | t = 0.1 ms to 10 ms, no voltage reappplied   |                            | 515.5   | 1013    | 1190    | kA <sup>2</sup> √s |
| Low level value of threshold voltage                           | $V_{T(TO)1}$  | (16.7 % $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$ ), $T_J$ maximum          |                            | 0.86    | 0.83    | 0.8     | V                  |
| High level value of threshold voltage                          | $V_{T(TO)2}$  | (I > $\pi \times I_{T(AV)}$ ), $T_J$ maximum   |                            | 1.05    | 1       | 0.98    |                    |
| Low level value on-state slope resistance                      | $r_{t1}$      | (16.7 % $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$ ), $T_J$ maximum          |                            | 2.02    | 1.78    | 1.67    | mΩ                 |
| High level value on-state slope resistance                     | $r_{t2}$      | (I > $\pi \times I_{T(AV)}$ ), $T_J$ maximum   |                            | 1.65    | 1.43    | 1.38    |                    |
| Maximum on-state voltage drop                                  | $V_{TM}$      | $I_{TM} = \pi \times I_{T(AV)}$ , $T_J = 25^\circ\text{C}$ , 180° conduction               |                            | 1.57    | 1.55    | 1.54    | V                  |
| Maximum forward voltage drop                                   | $V_{FM}$      | $I_{TM} = \pi \times I_{T(AV)}$ , $T_J = 25^\circ\text{C}$ , 180° conduction               |                            | 1.57    | 1.55    | 1.54    | V                  |
| Maximum holding current  | $I_H$         | Anode supply = 6 V initial $I_T = 30$ A, $T_J = 25^\circ\text{C}$                          |                            | 200     |         | mA      |                    |
| Maximum latching current                                       | $I_L$         | Anode supply = 6 V resistive load = 1 Ω Gate pulse: 10 V, 100 μs, $T_J = 25^\circ\text{C}$ |                            | 400     |         |         |                    |

| SWITCHING             |          |  |  |           |       |
|-----------------------|----------|--|--|-----------|-------|
| PARAMETER             | SYMBOL   | TEST CONDITIONS  |  | VALUES    | UNITS |
| Typical delay time    | $t_{gd}$ | $T_J = 25^\circ\text{C}$   | Gate current = 1 A, $di_g/dt = 1$ A/μs<br>$V_d = 0.67$ % $V_{DRM}$ | 1         | μs    |
| Typical rise time     | $t_{gr}$ |  |  | 2         |       |
| Typical turn-off time | $t_q$    | $I_{TM} = 300$ A, - $di/dt = 15$ A/μs; $T_J = T_J$ maximum<br>$V_R = 50$ V; $dV/dt = 20$ V/μs; gate 0 V, 100 Ω |  | 50 to 200 |       |

| BLOCKING   |                          |  |  |        |       |
|--|--------------------------|--|--|--------|-------|
| PARAMETER  | SYMBOL                   | TEST CONDITIONS  |  | VALUES | UNITS |
| Maximum peak reverse and off-state leakage current | $I_{RRM}$ ,<br>$I_{DRM}$ | $T_J = 125^\circ\text{C}$                                |  | 50     | mA    |
| RMS insulation voltage                             | $V_{INS}$                | 50 Hz, circuit to base, all terminals shorted, t = 1 s   |  | 3500   | V     |
| Critical rate of rise of off-state voltage         | $dV/dt$                  | $T_J = T_J$ maximum, exponential to 67 % rated $V_{DRM}$ |  | 1000   | V/μs  |


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| TRIGGERING                                  |             |   |   |        |            |
|---|-------------|---|---|--------|------------|
| PARAMETER                                   | SYMBOL      | TEST CONDITIONS   |   | VALUES | UNITS      |
| Maximum peak gate power                     | $P_{GM}$    | $t_p \leq 5$ ms, $T_J = T_J$ maximum                          |   | 12     | W          |
| Maximum average gate power                  | $P_{G(AV)}$ | $f = 50$ Hz, $T_J = T_J$ maximum                              |   | 3      |            |
| Maximum peak gate current                   | $I_{GM}$    | $t_p \leq 5$ ms, $T_J = T_J$ maximum                          |   | 3      | A          |
| Maximum peak negative gate voltage          | $-V_{GT}$   |   |   | 10     | V          |
| Maximum required DC gate voltage to trigger | $V_{GT}$    | $T_J = -40$ °C  | Anode supply = 6 V,<br>resistive load; $R_a = 1$ $\Omega$ | 4      |            |
|   |             | $T_J = 25$ °C   |   | 2.5    |            |
|   |             | $T_J = T_J$ maximum   |   | 1.7    |            |
| Maximum required DC gate current to trigger | $I_{GT}$    | $T_J = -40$ °C  |   | 270    | mA         |
|   |             | $T_J = 25$ °C   |   | 150    |            |
|   |             | $T_J = T_J$ maximum   |   | 80     |            |
| Maximum gate voltage that will not trigger  | $V_{GD}$    | $T_J = T_J$ maximum, rated $V_{DRM}$ applied                  |   | 0.3    | V          |
| Maximum gate current that will not trigger  | $I_{GD}$    |   |   | 10     | mA         |
| Maximum rate of rise of turned-on current   | $di/dt$     | $T_J = T_J$ maximum, $I_{TM} = 400$ A rated $V_{DRM}$ applied |   | 300    | A/ $\mu$ s |

| THERMAL AND MECHANICAL SPECIFICATIONS                     |                                  |  |             |         |         |       |
|---|----------------------------------|--|-------------|---------|---------|-------|
| PARAMETER   | SYMBOL                           | TEST CONDITIONS  | VSK.136     | VSK.142 | VSK.162 | UNITS |
| Maximum junction operating temperature range              | $T_J$                            |  | -40 to +125 |         |         | °C    |
| Maximum storage temperature range                         | $T_{Stg}$                        |  | -40 to +150 |         |         |       |
| Maximum thermal resistance, junction to case per junction | $R_{thJC}$                       | DC operation   | 0.18        | 0.18    | 0.16    | K/W   |
| Maximum thermal resistance, case to heatsink per module   | $R_{thCS}$                       | Mounting surface, smooth, flat and greased   | 0.05        |         |         |       |
| Mounting torque $\pm 10$ %                                | IAP to heatsink<br>busbar to IAP | A mounting compound is recommended and the torque should be rechecked after a period of 3 hours to allow for the spread of the compound. Lubricated threads. | 4 to 6      |         |         | Nm    |
| Approximate weight  |                                  |  | 200         |         |         | g     |
| Case style  |                                  |  | 7.1         |         |         | oz.   |
|   |                                  |  | INT-A-PAK   |         |         |       |

| $\Delta R$ CONDUCTION PER JUNCTION |  |        |        |        |        |   |        |        |        |        |       |
|------------------------------------|--|--------|--------|--------|--------|---|--------|--------|--------|--------|-------|
| DEVICES                            | SINUSOIDAL CONDUCTION AT $T_J$ MAXIMUM |        |        |        |        | RECTANGULAR CONDUCTION AT $T_J$ MAXIMUM |        |        |        |        | UNITS |
|                                    | 180°                                   | 120°   | 90°    | 60°    | 30°    | 180°                                    | 120°   | 90°    | 60°    | 30°    |       |
| VSK.136                            | 0.007                                  | 0.01   | 0.013  | 0.0155 | 0.017  | 0.009                                   | 0.012  | 0.014  | 0.015  | 0.017  | K/W   |
| VSK.142                            | 0.0019                                 | 0.0019 | 0.0020 | 0.0020 | 0.0021 | 0.0018                                  | 0.0022 | 0.0023 | 0.0023 | 0.0020 |       |
| VSK.162                            | 0.0030                                 | 0.0031 | 0.0032 | 0.0033 | 0.0034 | 0.0029                                  | 0.0036 | 0.0039 | 0.0041 | 0.0040 |       |

**Note**

- Table shows the increment of thermal resistance  $R_{thJC}$  when devices operate at different conduction angles than DC



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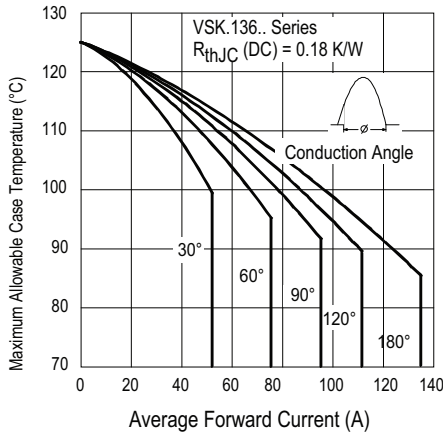


Fig. 1 - Current Ratings Characteristics

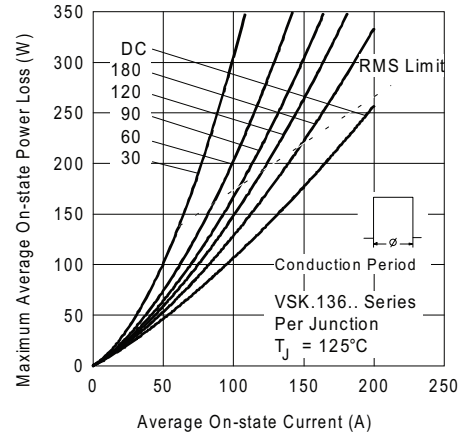


Fig. 4 - On-State Power Loss Characteristics

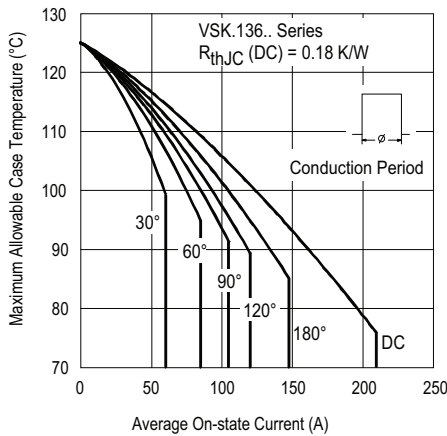


Fig. 2 - Current Ratings Characteristics

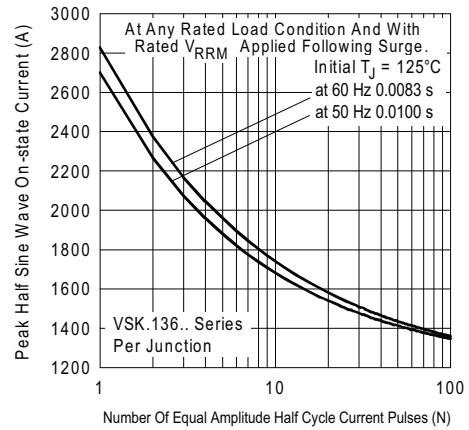


Fig. 5 - Maximum Non-Repetitive Surge Current

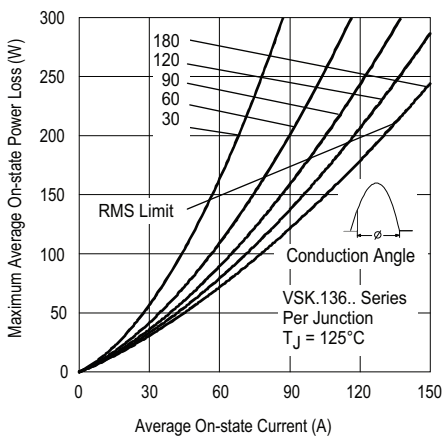


Fig. 3 - On-State Power Loss Characteristics

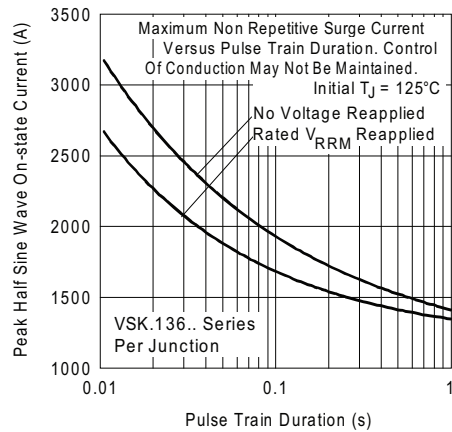


Fig. 6 - Maximum Non-Repetitive Surge Current



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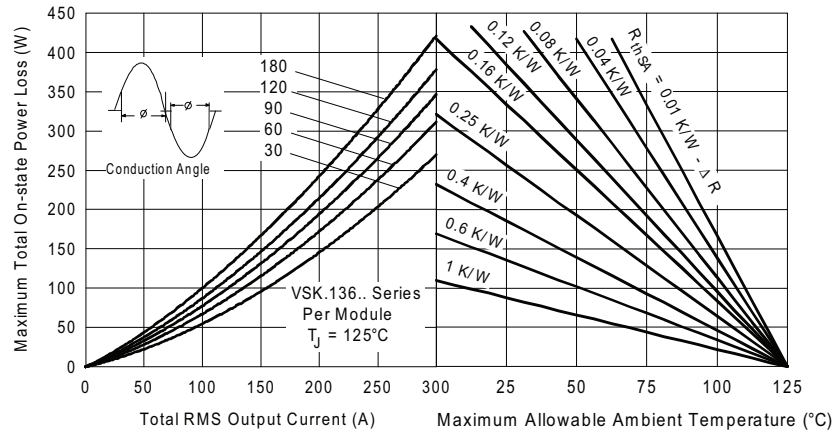


Fig. 7 - On-State Power Loss Characteristics

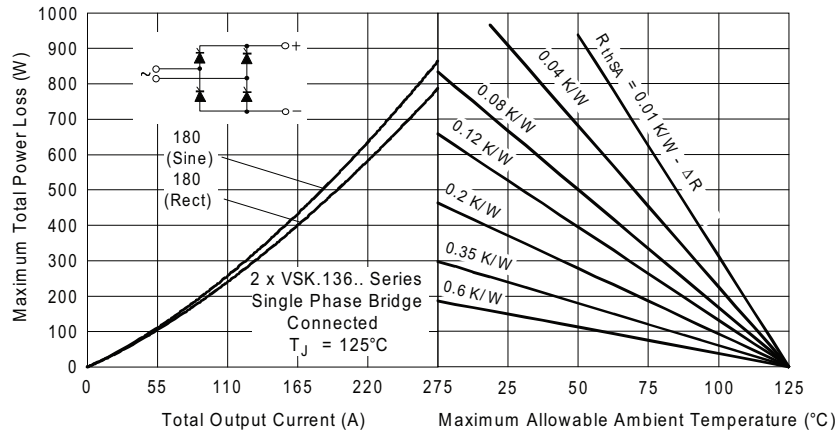


Fig. 8 - On-State Power Loss Characteristics

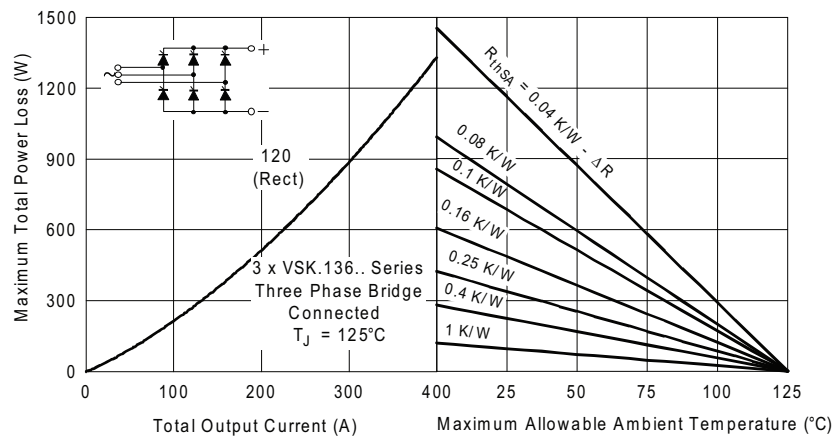


Fig. 9 - On-State Power Loss Characteristics



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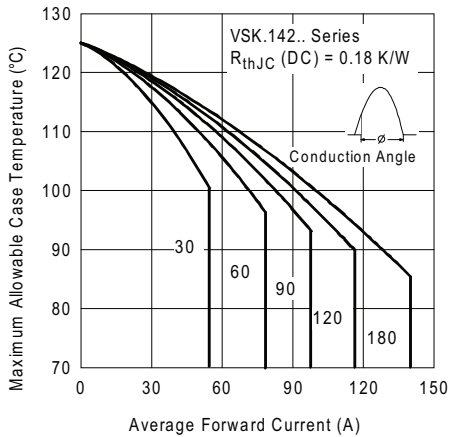


Fig. 10 - Current Ratings Characteristics

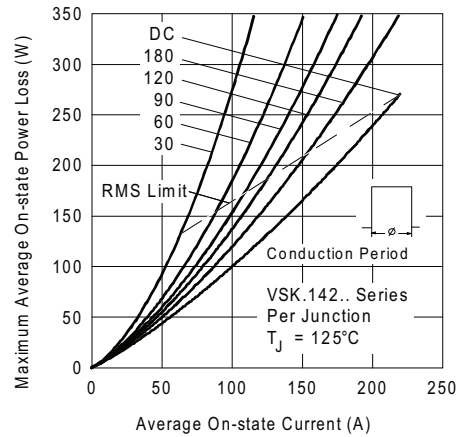


Fig. 13 - On-State Power Loss Characteristics

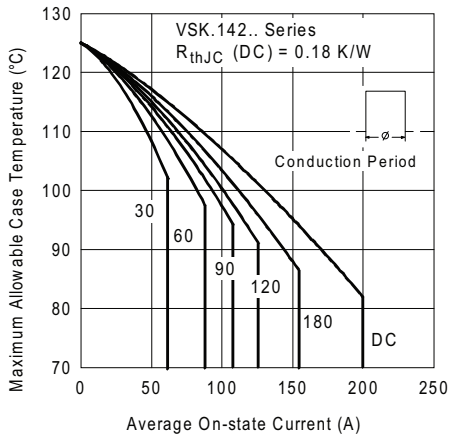


Fig. 11 - Current Ratings Characteristics

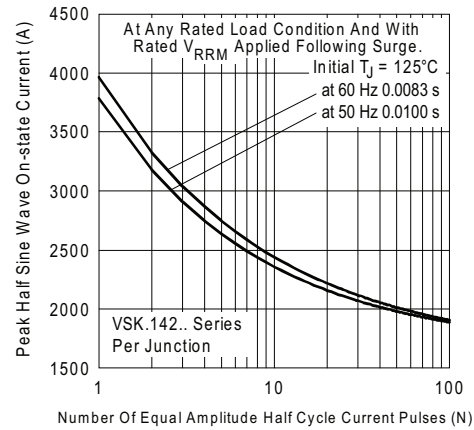


Fig. 14 - Maximum Non-Repetitive Surge Current

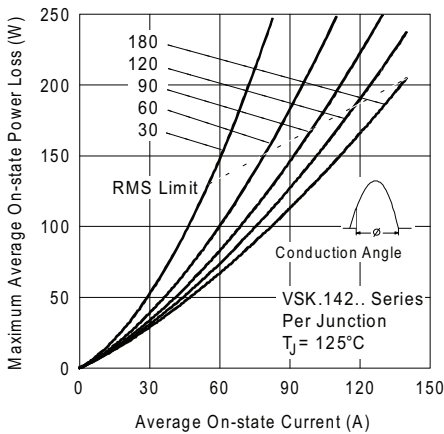


Fig. 12 - On-State Power Loss Characteristics

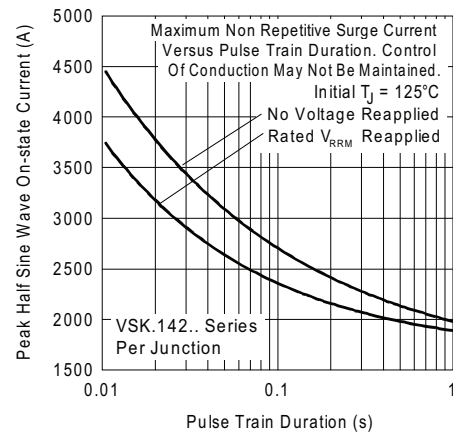


Fig. 15 - Maximum Non-Repetitive Surge Current



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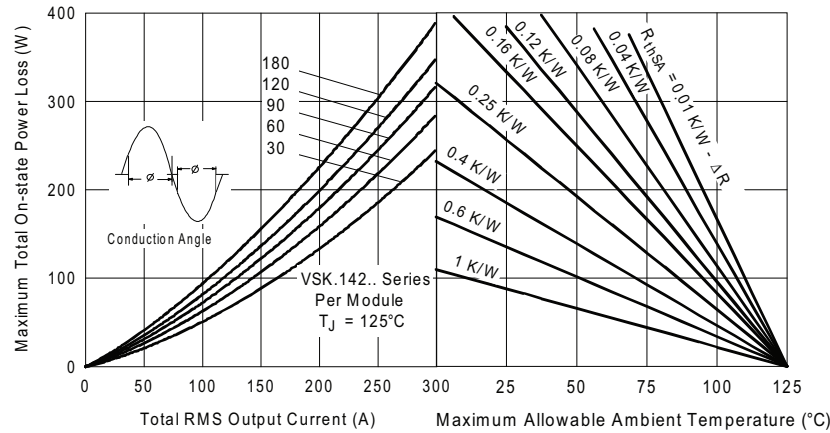


Fig. 16 - On-State Power Loss Characteristics

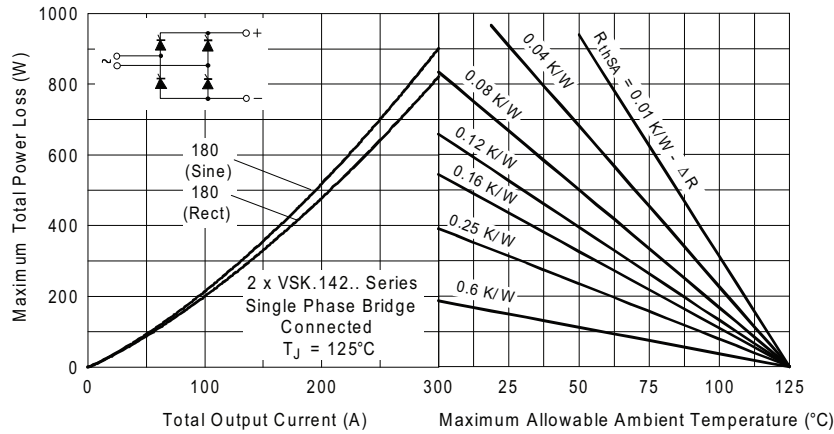


Fig. 17 - On-State Power Loss Characteristics

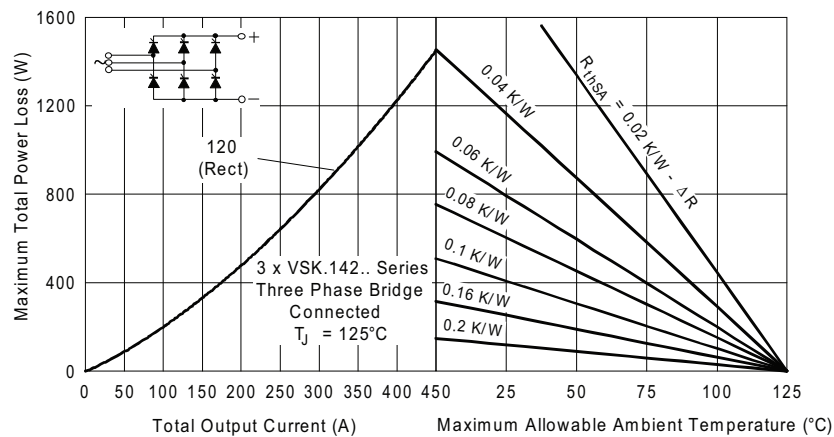


Fig. 18 - On-State Power Loss Characteristics



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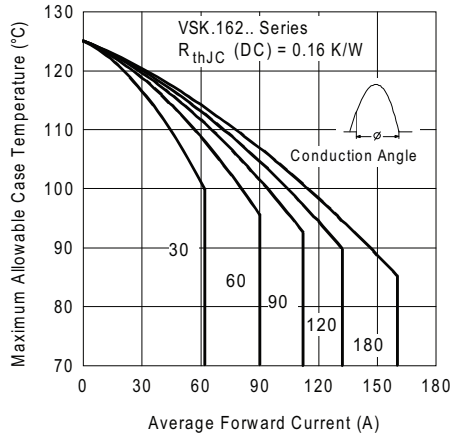


Fig. 19 - Current Ratings Characteristics

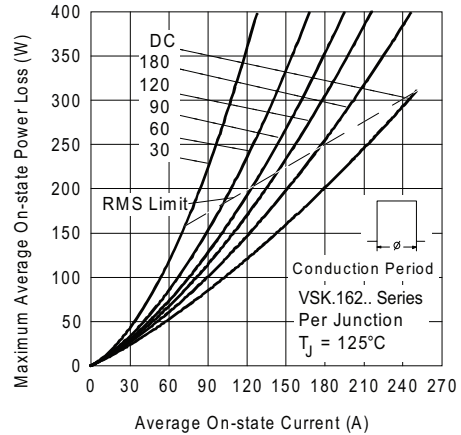


Fig. 22 - On-State Power Loss Characteristics

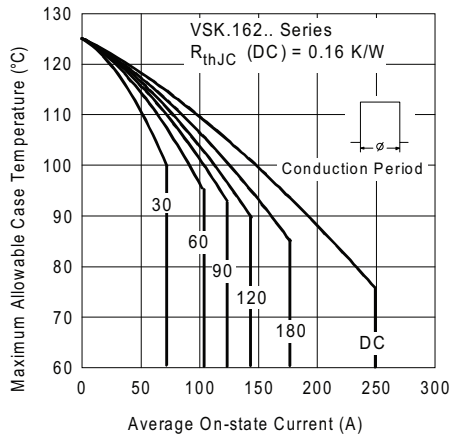


Fig. 20 - Current Ratings Characteristics

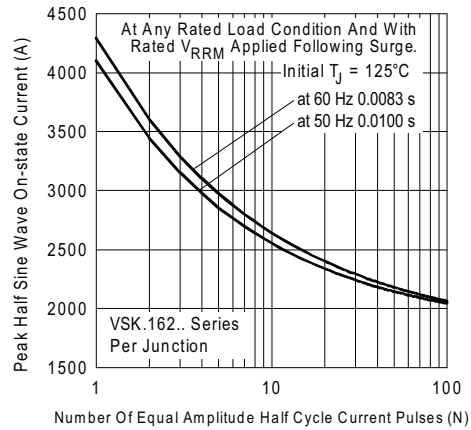


Fig. 23 - Maximum Non-Repetitive Surge Current

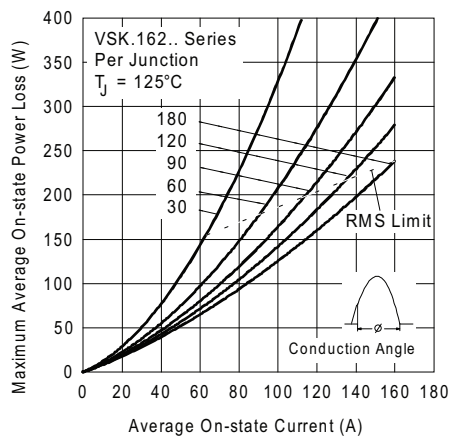


Fig. 21 - On-State Power Loss Characteristics

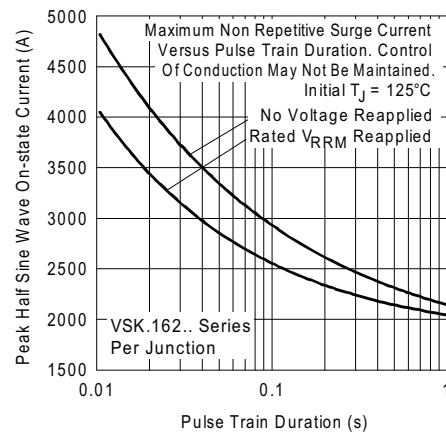


Fig. 24 - Maximum Non-Repetitive Surge Current



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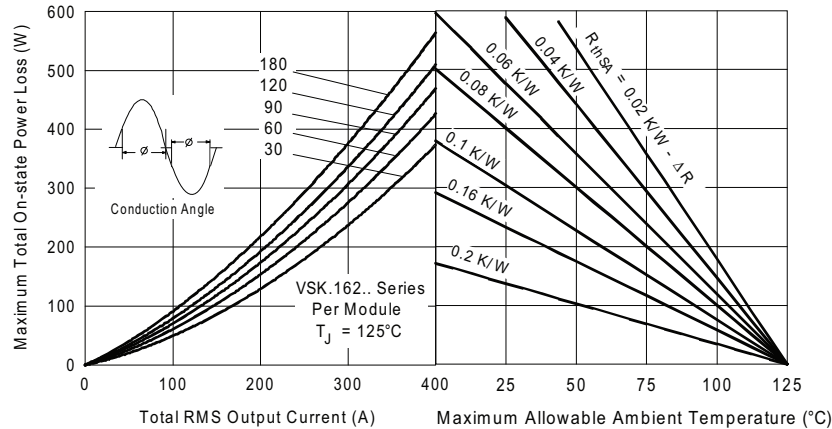


Fig. 25 - On-State Power Loss Characteristics

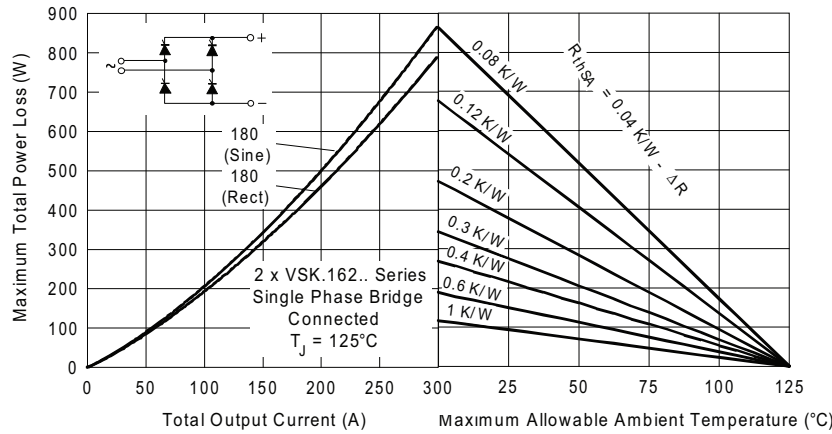


Fig. 26 - On-State Power Loss Characteristics

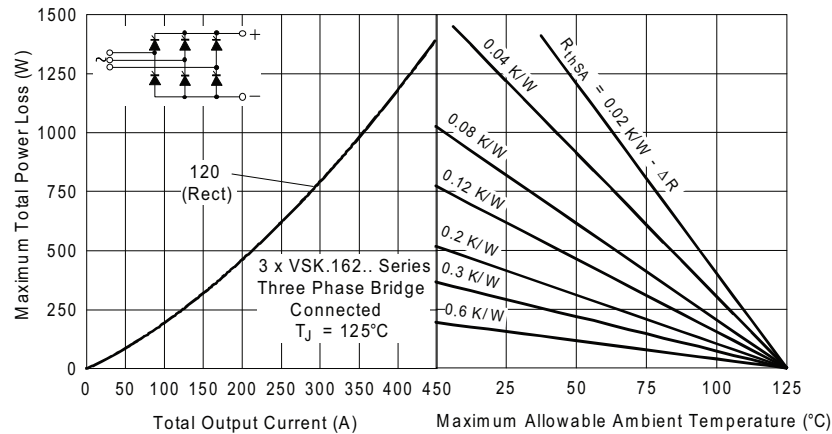


Fig. 27 - On-State Power Loss Characteristics



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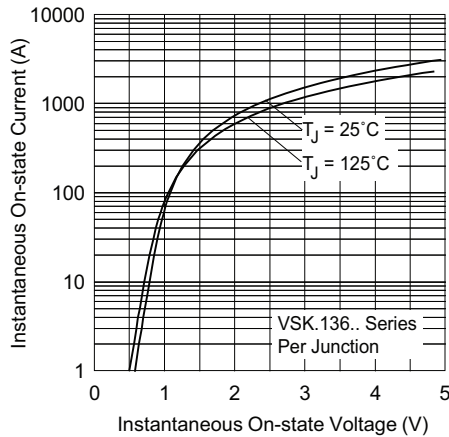


Fig. 28 - On-State Voltage Drop Characteristics

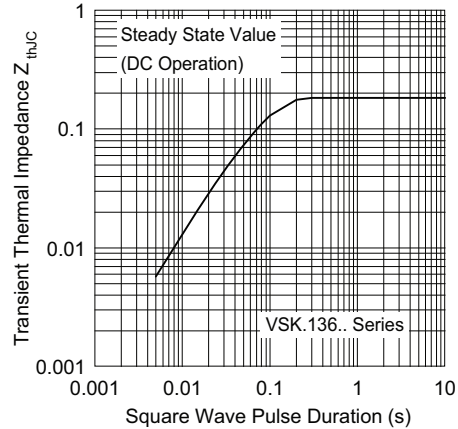


Fig. 31 - Thermal Impedance  $Z_{thJC}$  Characteristics

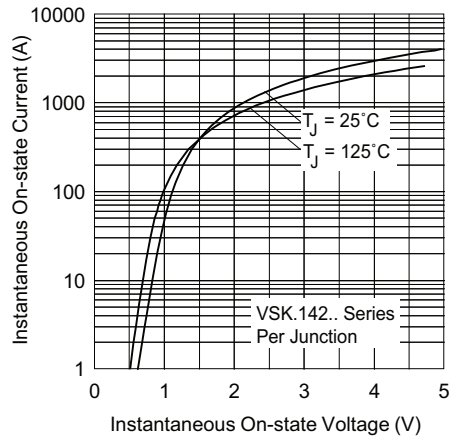


Fig. 29 - On-State Voltage Drop Characteristics

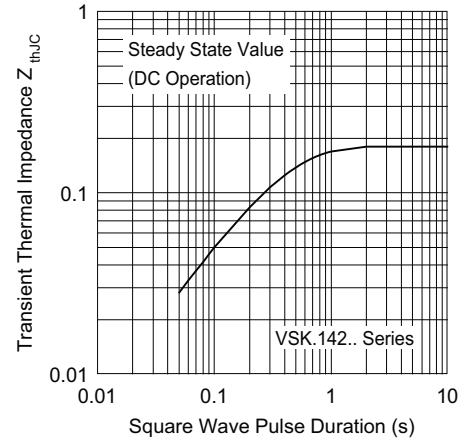


Fig. 32 - Thermal Impedance  $Z_{thJC}$  Characteristics

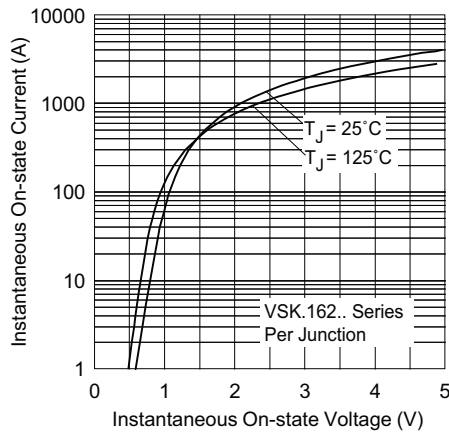


Fig. 30 - On-State Voltage Drop Characteristics

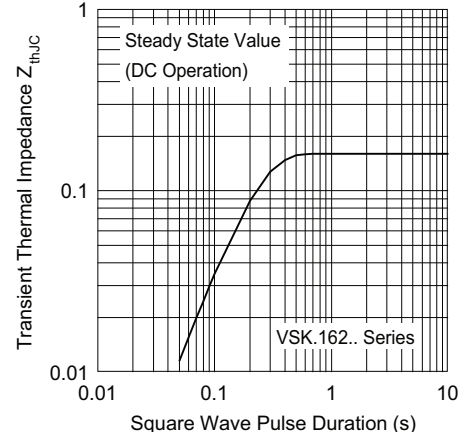


Fig. 33 - Thermal Impedance  $Z_{thJC}$  Characteristics



# VS-VSK.136..PbF, VS-VSK.142..PbF, VS-VSK.162..PbF Series

[www.vishay.com](http://www.vishay.com)

Vishay Semiconductors

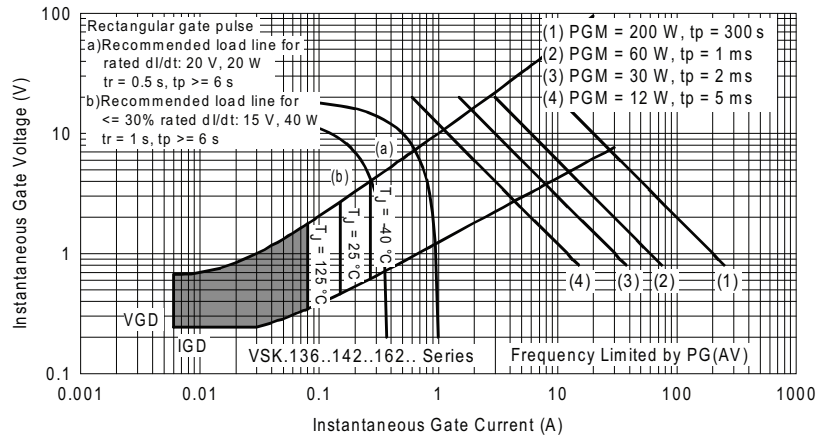


Fig. 34 - Gate Characteristics

## ORDERING INFORMATION TABLE

|             |              |           |                                |           |            |
|-------------|--------------|-----------|--------------------------------|-----------|------------|
| Device code | <b>VS-VS</b> | <b>KT</b> | <b>162</b>                     | <b>16</b> | <b>PbF</b> |
|             | ①            | ②         | ③                              | ④         | ⑤          |
|             | <b>1</b>     | -         | Vishay Semiconductors product  |           |            |
|             | <b>2</b>     | -         | Circuit configuration          |           |            |
|             | <b>3</b>     | -         | Current rating: $I_{T(AV)}$    |           |            |
|             | <b>4</b>     | -         | Voltage code x 100 = $V_{RRM}$ |           |            |
|             | <b>5</b>     | -         | PbF = Lead (Pb)-free           |           |            |

### Note

- To order the optional hardware go to [www.vishay.com/doc?95172](http://www.vishay.com/doc?95172)



**VS-VSK.136..PbF, VS-VSK.142..PbF, VS-VSK.162..PbF Series**

[www.vishay.com](http://www.vishay.com)

Vishay Semiconductors

| CIRCUIT CONFIGURATION                       |                            |                 |
|---|----------------------------|-----------------|
| CIRCUIT DESCRIPTION                         | CIRCUIT CONFIGURATION CODE | CIRCUIT DRAWING |
| Two SCRs doubler circuit                    | T                          |                 |
| SCR/diode doubler circuit, positive control | H                          |                 |
| SCR/diode doubler circuit, negative control | L                          |                 |

| LINKS TO RELATED DOCUMENTS |  |
|----------------------------|--|
| Dimensions                 | <a href="http://www.vishay.com/doc?95067">www.vishay.com/doc?95067</a> |

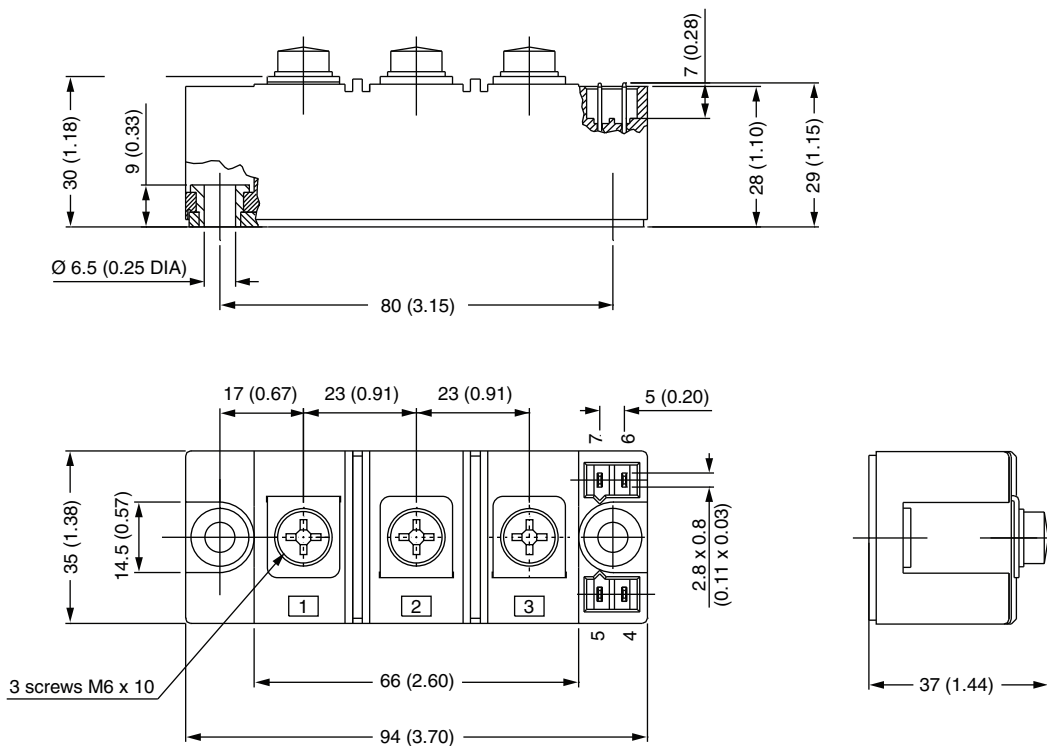


# Outline Dimensions

Vishay Semiconductors

## INT-A-PAK IGBT/Thyristor

**DIMENSIONS** in millimeters (inches)





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